

Absolute Maximum Ratings at $T_j=25\text{ }^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	V_{DS}	60	V
Gate source voltage	V_{GS}	± 20	V
Continuous drain current ¹⁾ , $T_c=25\text{ }^\circ\text{C}$	I_D	160	A
Pulsed drain current ²⁾ , $T_c=25\text{ }^\circ\text{C}$	$I_{D,\text{pulse}}$	480	A
Continuous diode forward current ¹⁾ , $T_c=25\text{ }^\circ\text{C}$	I_S	160	A
Diode pulsed current ²⁾ , $T_c=25\text{ }^\circ\text{C}$	$I_{S,\text{Pulse}}$	480	A
Power dissipation ³⁾ , $T_c=25\text{ }^\circ\text{C}$	P_D	168	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	200	mJ
Operation and storage temperature	$T_{stg} \ T_j$	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{th(j-c)}$	0.89	$^\circ\text{C}/\text{W}$
Thermal resistance, junction-ambient ⁴⁾	$R_{th(j-a)}$	62	$^\circ\text{C}/\text{W}$

Electrical Characteristics at $T_j=25\text{ }^\circ\text{C}$ unless otherwise specified

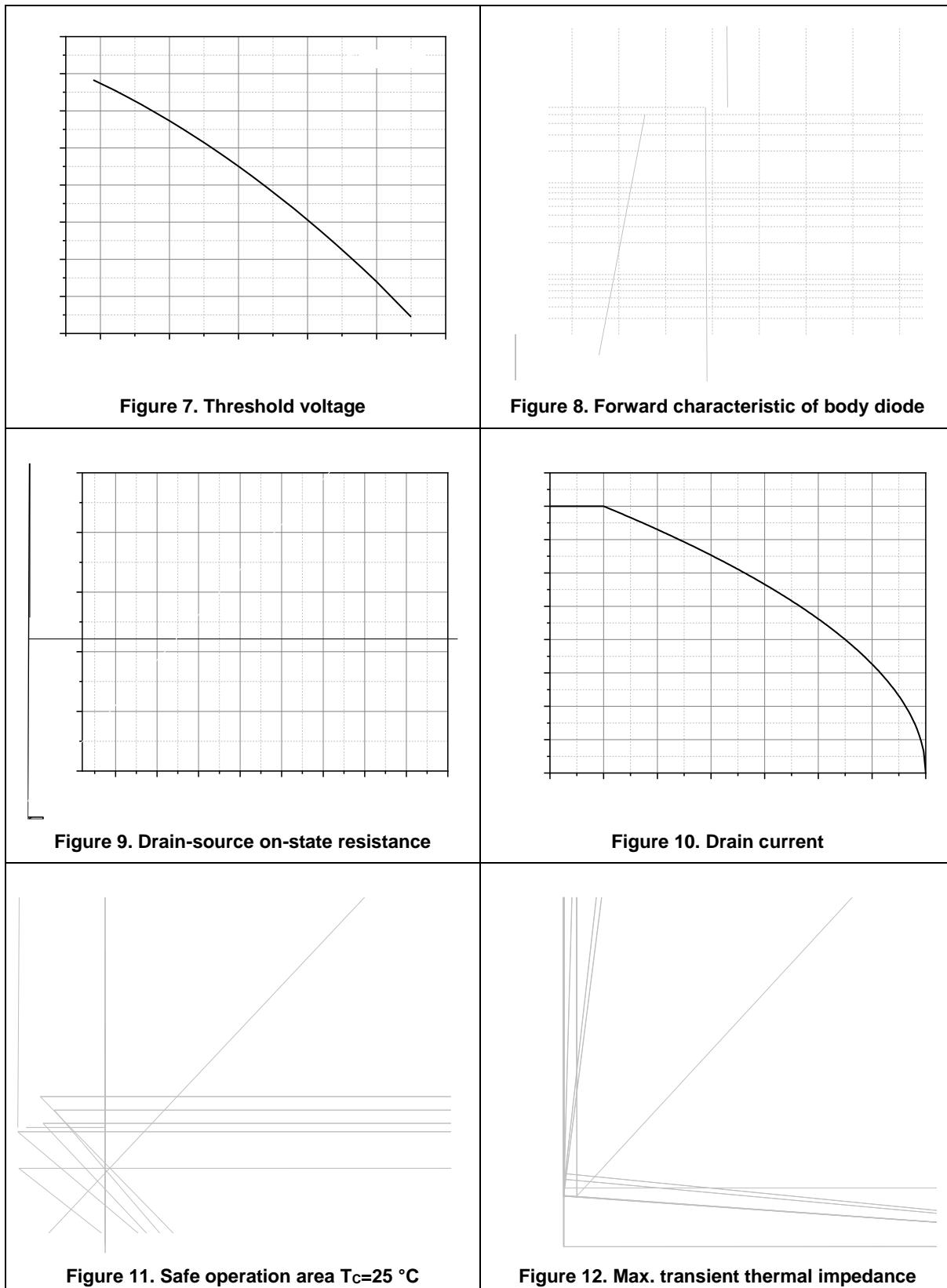
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	60			V	$V_{GS}=0\text{ V}$, $I_D=250\text{ A}$
Gate threshold voltage	$V_{GS(\text{th})}$	1.3		2.5	V	$V_{DS}=V_{GS}$, $I_D=250\text{ A}$
Drain-source on-state resistance	$R_{DS(\text{ON})}$		3.0	3.5		$V_{GS}=10\text{ V}$, $I_D=20\text{ A}$
Drain-source on-state resistance	$R_{DS(\text{ON})}$		3.5	4.5		$V_{GS}=4.5\text{ V}$, $I_D=10\text{ A}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=20\text{ V}$
				-100		$V_{GS}=-20\text{ V}$
Drain-source leakage current	I_{DSS}			1	A	$V_{DS}=60\text{ V}$, $V_{GS}=0\text{ V}$

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C _{iss}		5377		pF	V _{GS} =0 V, V _{DS} =25 V, 0 kHz
Output capacitance	C _{oss}		1666		pF	
Reverse transfer capacitance	C _{rss}		77.7		pF	
Turn-on delay time	t _{d(on)}		22.5		ns	V _{GS} =10 V, V _{DS} =30 V, R _{G0} I _D =25 A
Rise time	t _r		6.7		ns	
Turn-off delay time	t _{d(off)}		80.3		ns	
Fall time	t _f		26.8		ns	

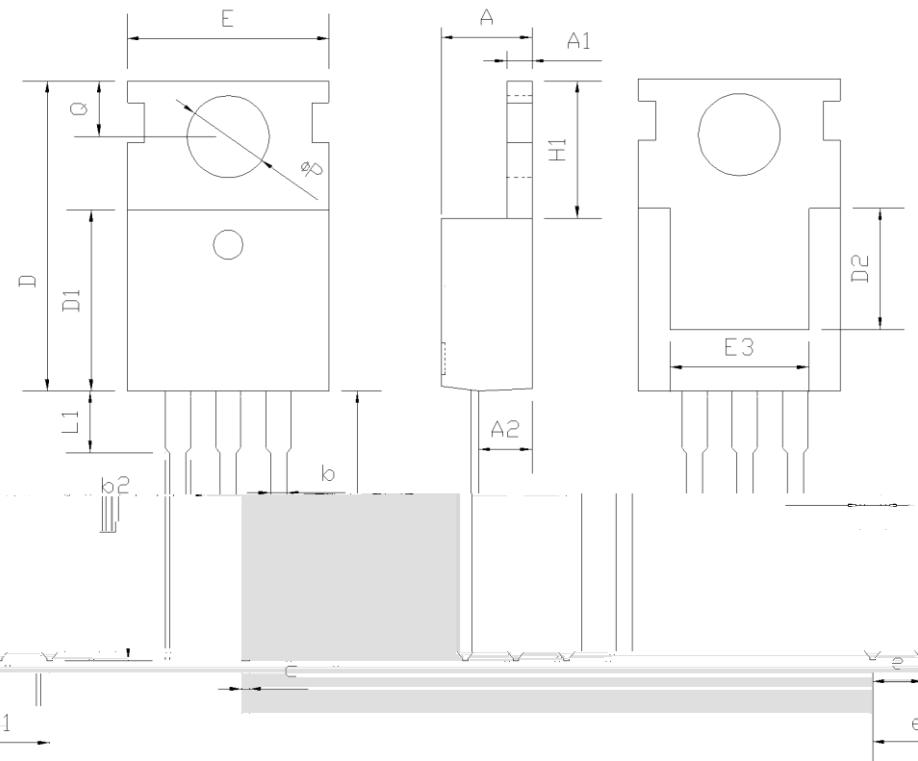
Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q _g		66.1		nC	V _{GS} =10 V, V _{DS} =30 V, I _D =25 A
Gate-source charge	Q _{gs}		10.7			



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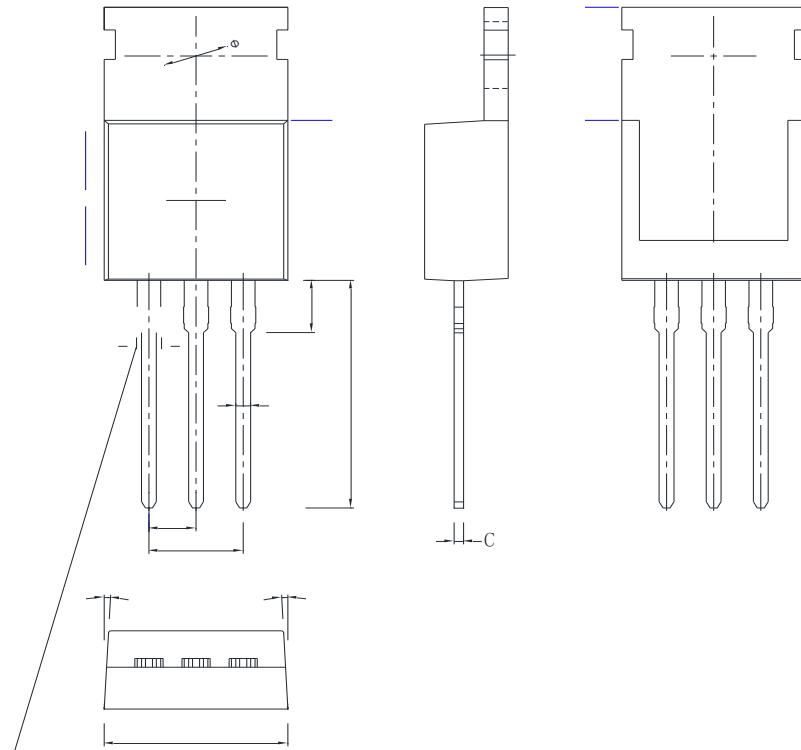
Package Information



Symbol	mm		
	Min	Nom	Max
A	4.37	4.57	4.77
A1	1.25	1.30	1.45
A2	2.20	2.40	2.60
b	0.70	0.80	0.95
b2	1.17	1.27	1.47
c	0.40	0.50	0.65
D	15.10	15.60	16.10
D1	8.80	9.10	9.40
D2	5.50	-	-
E	9.70	10.00	10.30
E3	7.00	-	-
e	2.54 BSC		
e1	5.08 BSC		
H1	6.25	6.50	6.85
L	12.75	13.50	13.80
L1	-	3.10	3.40
C	3.40	3.60	3.80
Q	2.60	2.80	3.00

Version 1: TO220-C package outline dimension

Package Information



Symbol	mm		
	Min	Nom	Max
A	4.40	4.50	4.60
A1	1.27	1.30	1.33
A2	2.30	2.40	2.50
b	0.70	-	0.90
b1	1.27	-	1.40
c	0.45	0.50	0.60
D	15.30	15.70	16.10
D1	9.10	9.20	9.30
D2	13.10	-	13.70
E	9.70	9.90	10.20
E1	7.80	8.00	8.20
e	2.54 BSC		
e1	5.08 BSC		
H1	6.30	6.50	6.70
L	12.78	13.08	13.38
L1	-	-	3.50
L2	4.60 REF		
C	3.55	3.60	3.65
Q	2.73	-	2.87
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Version 2: TO220-J package outline dimension

Ordering Information

Package Type	Units/ Tube	Tubes / Inner Box	Units/ Inner Box	Inner Boxes/
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